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Vishay Siliconix

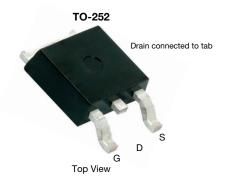
Automotive N-Channel 50 V (D-S) 175 °C MOSFET

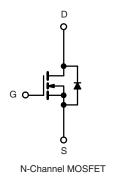
PRODUCT SUMMARY				
V _{DS} (V)	50			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.011			
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.015			
I _D (A)	50			
Configuration	Single			
Package	TO-252			

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified d
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912







ABSOLUTE MAXIMUM RATING	GS (T _C = 25 °C, unles	s otherwise noted	d)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	50	
Gate-Source Voltage		V _{GS} ± 20		V
Continuous Drain Current	T _C = 25 °C ^a	I _D	50	
Continuous Drain Current	T _C = 125 °C		32	
Continuous Source Current (Diode Conduction) a		I _S	50	Α
Pulsed Drain Current ^b		I _{DM}	200	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	22.5	
Single Pulse Avalanche Energy	L = U.1 IIII	E _{AS}	25.3	mJ
Maximum Dawar Dissination h	T _C = 25 °C	D	75	W
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	25	VV
Operating Junction and Storage Temperature Range		T _J , T _{sta}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount c	R_{thJA}	60	°C/W
Junction-to-Case (Drain)			2	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} =	= 0 V, I _D = 250 μA	50	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 50 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 50 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 50 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
		V _{GS} = 10 V	I _D = 45 A	-	0.009	0.011	
Drain-Source On-State Resistance a		V _{GS} = 10 V	I _D = 45 A, T _J = 125 °C	-	-	0.020	Ω
	R _{DS(on)}	V _{GS} = 10 V	I _D = 45 A, T _J = 175 °C	-	-	0.024	
		V _{GS} = 4.5 V	I _D = 20 A	-	-	0.015	
Forward Transconductance b	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	58	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	1685	2106	
Output Capacitance	Coss	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	345	430	рF
Reverse Transfer Capacitance	C _{rss}	1		-	144	180	
Total Gate Charge ^c	Qg			-	34.6	52	
Gate-Source Charge c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 25 \text{ V}, I_D = 43 \text{ A}$	-	5.5	9	nC
Gate-Drain Charge ^c	Q_{gd}	1		-	9.1	14]
Gate Resistance	R_g		f = 1 MHz		1.8	3.9	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	8.5	13	
Rise Time ^c	t _r	$V_{DD} = 25 \text{ V}, R_L = 0.6 \Omega$		-	11.5	18	200
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 43 \text{ A},$	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	22.5	34	ns
Fall Time ^c	t _f]		-	7.5	12	
Source-Drain Diode Ratings and Chara	acteristics b						
Pulsed Current ^a	I _{SM}			-	-	200	Α
Forward Voltage	V_{SD}	I _F = 45 A, V _{GS} = 0 V		-	0.95	1.5	V

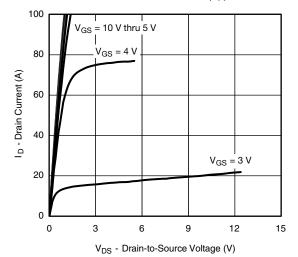
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

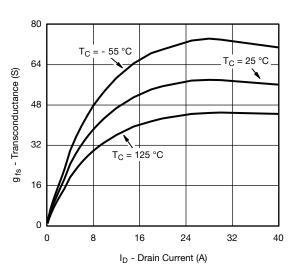
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



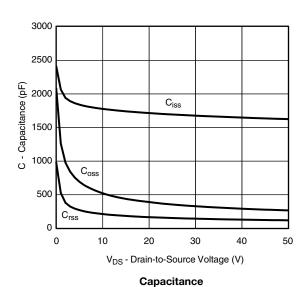
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

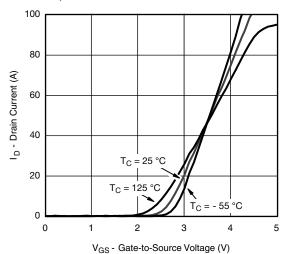


Output Characteristics

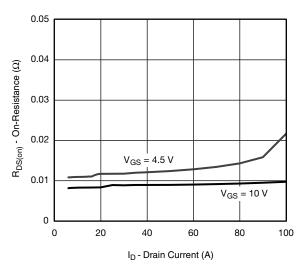


Transconductance

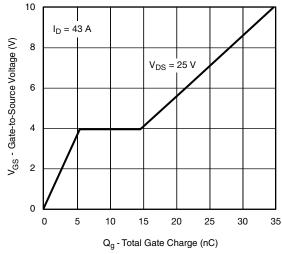




Transfer Characteristics



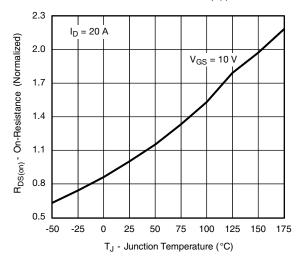
On-Resistance vs. Drain Current

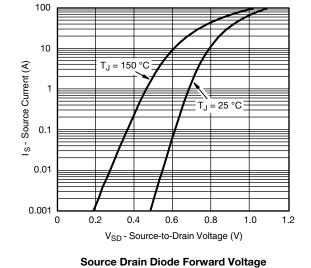


Gate Charge

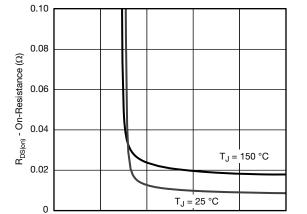


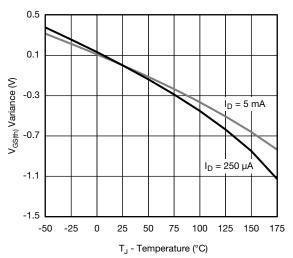
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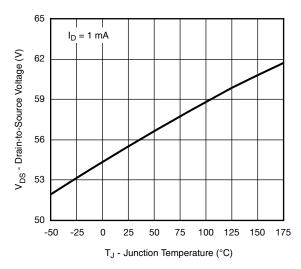


On-Resistance vs. Junction Temperature









10

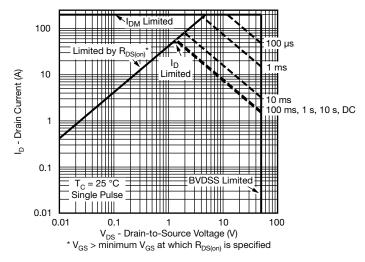
Drain Source Breakdown vs. Junction Temperature

0

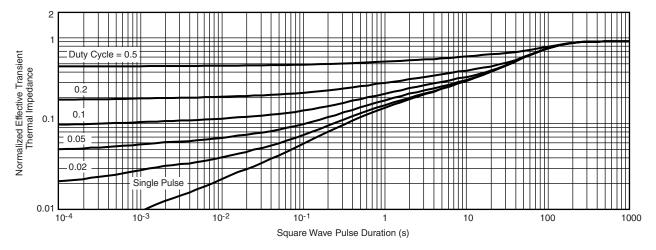
For technical questions, contact: automostech



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



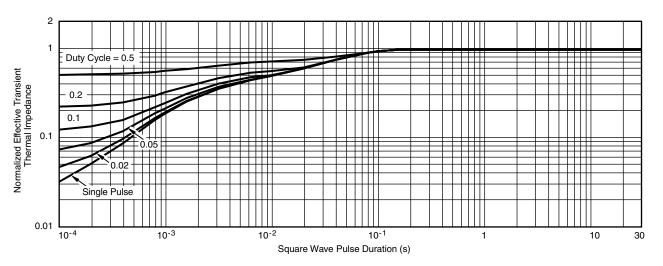
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg272168.



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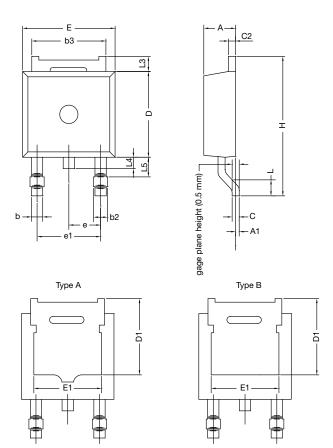
REVISION HISTORY ^a		
REVISION	DATE	DESCRIPTION OF CHANGE
D	04-Aug-15	Revised R _g minimum limit

Note

a. As of April 2014



TO-252AA Case Outline



DIM	MILLIN	MILLIMETERS		
DIM.	MIN.	MAX.	MIN.	MAX.
Α	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
Н	9.40	10.41	0.370	0.410
е	2.28	BSC	0.090	BSC
e1	4.56	BSC	0.180	BSC
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060

ECN: T25-0122-Rev. C, 12-May-2025 DWG: 6019

Notes

- Dimension L3 is for reference only
- Dimension D1 and E1 on type A and B is the same



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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